

Vishay Semiconductors

AAP Gen 7 (TO-240AA) Power Modules Thyristor/Thyristor, 75 A



ADD-A-PAK

PRIMARY CHARACTERISTICS					
I _{T(AV)}	75 A				
Туре	Modules - thyristor, standard				
Package	AAP Gen 7 (TO-240AA)				

MECHANICAL DESCRIPTION

The AAP Gen 7 (TO-240AA), new generation of AAP module, combines the excellent thermal performances obtained by the usage of exposed direct bonded copper substrate, with advanced compact simple package solution and simplified internal structure with minimized number of interfaces.

FEATURES

- · High voltage
- Industrial standard package



- UL approved file E78996
- · Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- Excellent thermal performances obtained by the usage of exposed direct bonded copper substrate
- Up to 1600 V
- · High surge capability
- · Easy mounting on heatsink

ELECTRICAL DESCRIPTION

These modules are intended for general purpose high voltage applications such as high voltage regulated power supplies, lighting circuits, temperature and motor speed control circuits, UPS and battery charger.

MAJOR RATINGS AND CHARACTERISTICS						
SYMBOL	CHARACTERISTICS	VALUES	UNITS			
I _{T(AV)}	85 °C	75				
I _{T(RMS)}		115	Α			
1	50 Hz	1300	A			
I _{TSM}	60 Hz	1360				
l ² t	50 Hz	8.45	kA ² s			
1-1	60 Hz	7.68	KA-S			
I ² √t		84.5	kA²√s			
V _{RRM}	Range	400 to 1600	V			
T _{Stg}		-40 to +125	°C			
TJ		-40 to +125	°C			



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ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS									
TYPE NUMBER	VOLTAGE CODE	V _{RRM} , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM REPETITIVE PEAK OFF-STATE VOLTAGE, GATE OPEN CIRCUIT V	I _{RRM,} I _{DRM} AT 125 °C mA				
	04	400	500	400					
VS-VSK.71	08	800	900	800	15				
V3-V3N./ I	12	1200	1300	1200	15				
	16	1600	1700	1600					

ON-STATE CONDUCTION							
PARAMETER	SYMBOL		TEST CONDITIONS				
Maximum average on-state current	I _{T(AV)}	180° conduction	180° conduction, half sine wave, T _C = 85 °C				
Maximum continuous RMS on-state current		DC			115	Α	
Maximum continuous RMS on-state current	I _{T(RMS)}	T _C			80	°C	
		t = 10 ms	No voltage		1300		
Maximum peak, one-cycle non-repetitive		t = 8.3 ms	reapplied	Sinusoidal	1360	٨	
on-state current	I _{TSM}	t = 10 ms	100 % V _{RRM}	half wave, initial $T_J = T_J$ maximum	1093	Α	
		t = 8.3 ms	reapplied		1140		
		t = 10 ms	No voltage		8.45		
Maximum I ² t for fusing	l ² t	t = 8.3 ms	reapplied	Initial $T_J = T_J$ maximum	7.68	kA ² s	
	1-1	t = 10 ms	100 % V _{RRM}		5.97		
		t = 8.3 ms	reapplied		5.45		
Maximum I²√t for fusing	I ² √t ⁽¹⁾		t = 0.1 ms to 10 ms, no voltage reapplied T _{.1} = T _{.1} maximum				
	(2)	Low level (3)			0.96	.,	
Maximum value of threshold voltage	V _{T(TO)} (2)	High level (4)	$T_J = T_J \text{ maxin}$	num	1.08	V	
Maximum value of on-state	(2)	Low level (3)	T T		3.28	0	
slope resistance	r _t ⁽²⁾	High level (4)	$T_J = T_J$ maximum		2.86	mΩ	
Maximum on-state voltage drop	V_{TM}	$I_{TM} = \pi \times I_{T(AV)}$ $T_J = 25 ^{\circ}C$			1.72	V	
Maximum non-repetitive rate of rise of turned on current	dl/dt	$T_J = 25 ^{\circ}\text{C}$, from 0.67 V_{DRM} , $I_{TM} = \pi x I_{T(AV)}$, $I_g = 500 \text{mA}$, $t_r < 0.5 \mu \text{s}$, $t_p > 6 \mu \text{s}$			150	A/µs	
Maximum holding current	I _H	T _J = 25 °C, and resistive load,	250	mA			
Maximum latching current	ΙL	T _J = 25 °C, and	ode supply = 6 \	/, resistive load	400		

Notes

 $^{^{(1)}}$ I^2t for time $t_x = I^2 \sqrt{t} \ x \ \sqrt{t_x}$

⁽²⁾ Average power = $V_{T(TO)} \times I_{T(AV)} + r_t \times (I_{T(RMS)})^2$

^{(3) 16.7 %} x π x $I_{AV} < I < \pi$ x I_{AV}

 $^{^{(4)}~}I>\pi~x~I_{AV}$



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TRIGGERING					
PARAMETER	SYMBOL	TEST CO	NDITIONS	VALUES	UNITS
Maximum peak gate power	P _{GM}			12	W
Maximum average gate power	P _{G(AV)}			3.0	VV
Maximum peak gate current	I _{GM}			3.0	Α
Maximum peak negative gate voltage	- V _{GM}			10	
	V _{GT}	T _J = - 40 °C	Anode supply = 6 V resistive load	4.0	V
Maximum gate voltage required to trigger		T _J = 25 °C		2.5	
		T _J = 125 °C		1.7	
		T _J = - 40 °C	Anode supply = 6 V	270	
Maximum gate current required to trigger	I _{GT}	T _J = 25 °C		150	mA
		T _J = 125 °C	- resistive load	80	
Maximum gate voltage that will not trigger	V_{GD}	T _J = 125 °C, rated V _{DRM} applied		0.25	V
Maximum gate current that will not trigger	I _{GD}	$T_J = 125 ^{\circ}\text{C}$, rated V_{DR}	_M applied	6	mA

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak reverse and off-state leakage current at V _{RRM} , V _{DRM}	I _{RRM,} I _{DRM}	T _J = 125 °C, gate open circuit	15	mA
Maximum RMS insulation voltage	V _{INS}	50 Hz	3000 (1 min) 3600 (1 s)	V
Maximum critical rate of rise of off-state voltage	dV/dt	T_J = 125 °C, linear to 0.67 V_{DRM}	1000	V/µs

THERMAL AND MECHANICAL SPECIFICATIONS								
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Junction operating and storage temperature range		T _J , T _{Stg}		-40 to +125	°C			
Maximum internal thermal resistance, junction to case per leg		R _{thJC}	DC operation	0.29	°C/W			
Typical thermal resistance, case to heatsink per module		R _{thCS}	Mounting surface flat, smooth and greased	0.1	C/VV			
Mounting torque ± 10 % to heatsink busbar			A mounting compound is recommended and the torque should be rechecked after a period of	4	Nime			
			3 hours to allow for the spread of the compound.	3	Nm			
Approximate weight				75	g			
				2.7	OZ.			
Case style			JEDEC®	AAP Gen 7	(TO-240AA)			

△R CONDUCTION PER JUNCTION											
DEVICES	5	SINE HALF	WAVE CO	NDUCTION	١	RE	CTANGUL	AR WAVE C	CONDUCTION	ON	UNITS
DEVICES	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	UNITS
VSK.71	0.052	0.062	0.079	0.116	0.197	0.037	0.064	0.085	0.121	0.200	°C/W

Note

Table shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

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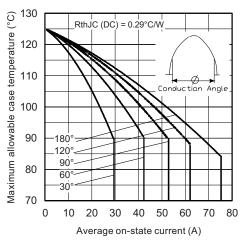


Fig. 1 - Current Ratings Characteristics

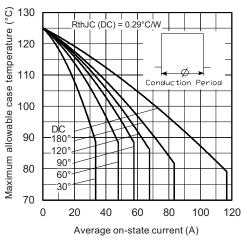


Fig. 2 - Current Ratings Characteristics

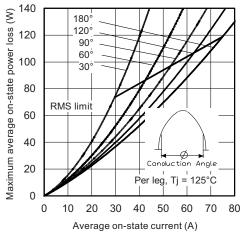


Fig. 3 - On-State Power Loss Characteristics

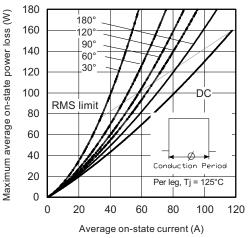
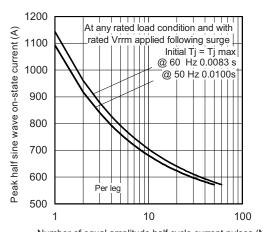


Fig. 4 - On-State Power Loss Characteristics



Number of equal amplitude half cycle current pulses (N)

Fig. 5 - Maximum Non-Repetitive Surge Current

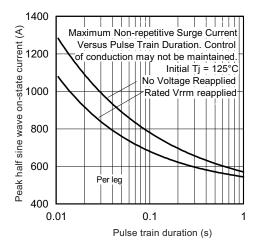


Fig. 6 - Maximum Non-Repetitive Surge Current

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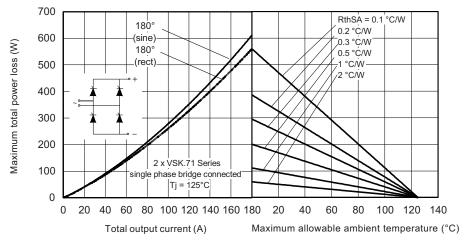


Fig. 7 - On-State Power Loss Characteristics

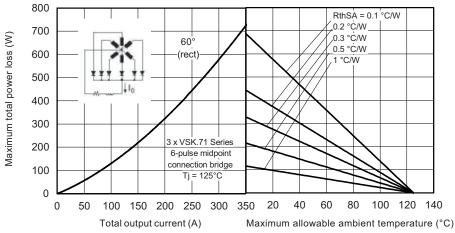


Fig. 8 - On-State Power Loss Characteristics

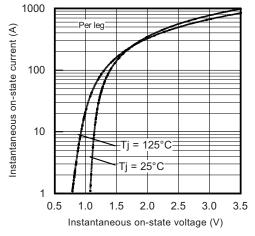


Fig. 9 - On-State Voltage Characteristics

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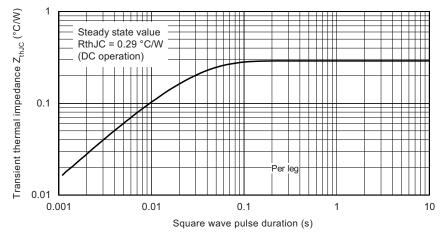


Fig. 10 - Thermal Impedance Z_{thJC} Characteristics

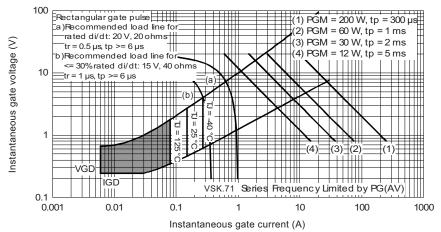
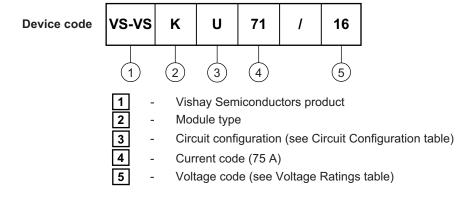


Fig. 11 - Gate Characteristics

ORDERING INFORMATION TABLE



Note

• To order the optional hardware go to www.vishay.com/doc?95172



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CIRCUIT CONFIGURATION								
CIRCUIT DESCRIPTION	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING						
Two SCRs common cathodes	U	VSKU (1) 1 2 (2) (3) (3) (3) (4) (5) (7) (6)						
Two SCRs common anodes	V	VSKV (1) 1 2 45 76 (3) (3) (3) (3) (4) (5) (7) (6)						

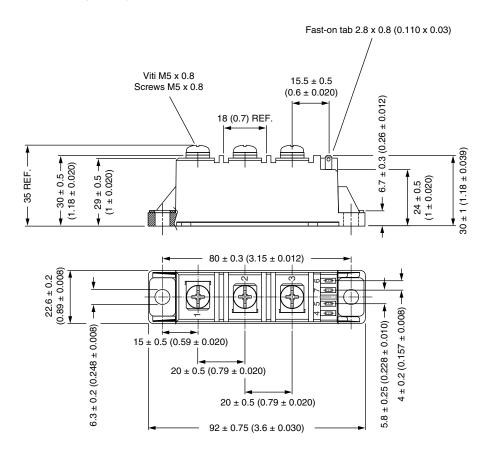
LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95368			



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ADD-A-PAK Generation VII - Thyristor

DIMENSIONS in millimeters (inches)





Legal Disclaimer Notice

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